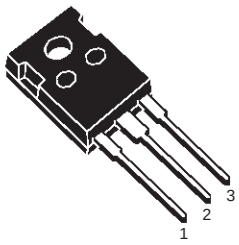
查询STW80NE06-10供应商

STW80NE06-10

N - CHANNEL 60V - 0.0085Ω - 80A - TO-247
STripFET™ " POWER MOSFET

TYPE	V_{DSS}	$R_{DS(on)}$	I_D
STW80NE06-10	60 V	<0.01 Ω	80 A

- TYPICAL $R_{DS(on)}$ = 0.0085 Ω
- EXCEPTIONAL dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- APPLICATION ORIENTED CHARACTERIZATION



TO-247

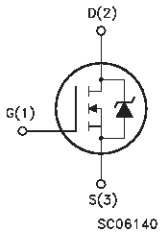
DESCRIPTION

This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

APPLICATIONS

- SOLENOID AND RELAY DRIVERS
- MOTOR CONTROL, AUDIO AMPLIFIERS
- DC-DC CONVERTERS
- AUTOMOTIVE ENVIRONMENT

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source Voltage (V_{GS} = 0)	60	V
V_{DGR}	Drain- gate Voltage (R_{GS} = 20 kΩ)	60	V
V_{GS}	Gate-source Voltage	± 20	V
I_D	Drain Current (continuous) at T_c = 25 °C	80	A
I_D	Drain Current (continuous) at T_c = 100 °C	57	A
I_{DM}(•)	Drain Current (pulsed)	320	A
P_{tot}	Total Dissipation at T_c = 25 °C	200	W
	Derating Factor	1.33	W/°C
dv/dt	Peak Diode Recovery voltage slope	7	V/ns
T_{stg}	Storage Temperature	-65 to 175	°C
T_j	Max. Operating Junction Temperature	175	°C

(•) Pulse width limited by safe operating area

(1) I_{SD} ≤ 80 A, di/dt ≤ 300 A/µs, V_{DD} ≤ $V_{(BR)DSS}$, T_j ≤ T_{JMAX}

THERMAL DATA

$R_{thj\text{-}case}$	Thermal Resistance Junction-case	Max	0.75	°C/W
$R_{thj\text{-}amb}$	Thermal Resistance Junction-ambient	Max	30	oC/W
$R_{thc\text{-}sink}$	Thermal Resistance Case-sink	Typ	0.1	°C/W
T_l	Maximum Lead Temperature For Soldering Purpose		300	°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	80	A
E_{AS}	Single Pulse Avalanche Energy (starting T_j = 25 °C, $I_D = I_{AR}$, V_{DD} = 30 V)	350	mJ

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 250 µA V_{GS} = 0	60			V
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0)	V_{DS} = Max Rating V_{DS} = Max Rating T_c = 125 °C			1 10	µA µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ± 20 V			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS} I_D = 250 µA	2	3	4	V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10V I_D = 40 A		8.5	10	mΩ
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ V_{GS} = 10 V	80			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (*)	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ I_D =40 A	19	38		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V_{DS} = 25 V f = 1 MHz V_{GS} = 0		7600 890 150	10000 1100 200	pF pF pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Time Rise Time	V_{DD} = 30 V I_D = 40 A R_G =4.7 Ω V_{GS} = 10 V (see test circuit, figure 3)		50 150	65 200	ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	V_{DD} = 48 V I_D = 80 A V_{GS} = 10 V		140 20 50		nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	V_{DD} = 48 V I_D = 40 A R_G =4.7 Ω V_{GS} = 10 V (see test circuit, figure 5)		45 75 130	60 100 170	ns ns ns

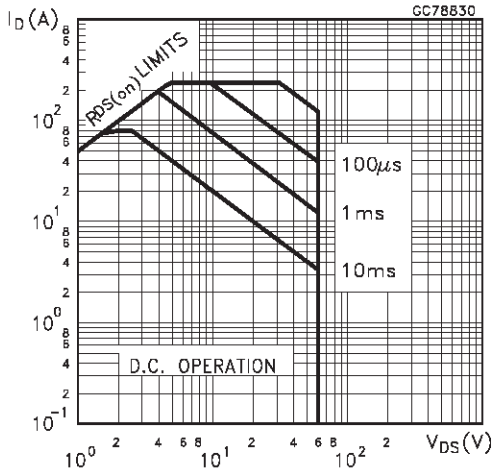
SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM}(•)	Source-drain Current Source-drain Current (pulsed)				80 320	A A
V_{SD} (*)	Forward On Voltage	I_{SD} = 80 A V_{GS} = 0			1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	I_{SD} = 80 A di/dt = 100 A/µs V_{DD} = 30 V T_j = 150 °C (see test circuit, figure 5)		100 0.4 8		ns µC A

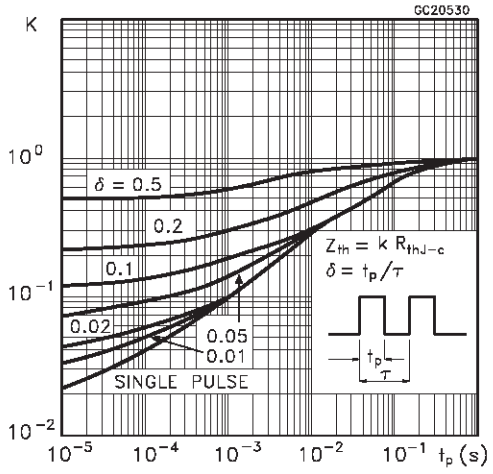
(*) Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %

(•) Pulse width limited by safe operating area

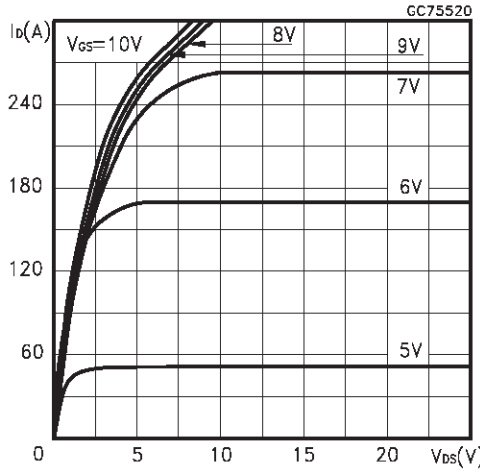
Safe Operating Area



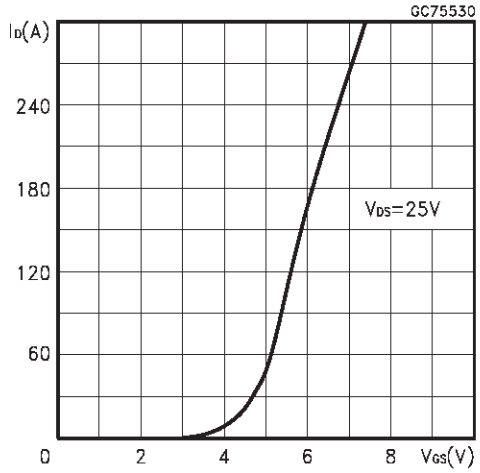
Thermal Impedance



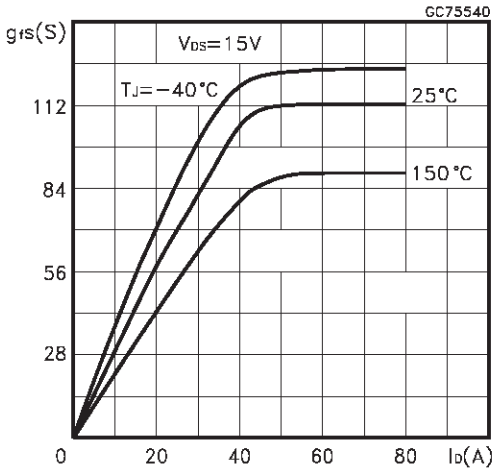
Output Characteristics



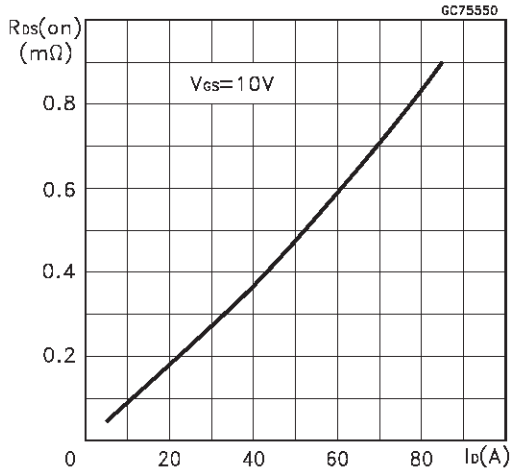
Transfer Characteristics



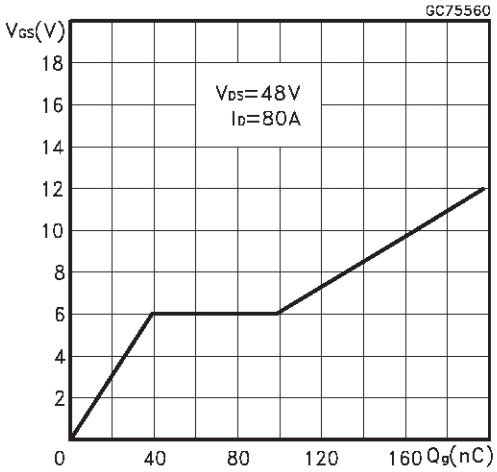
Transconductance



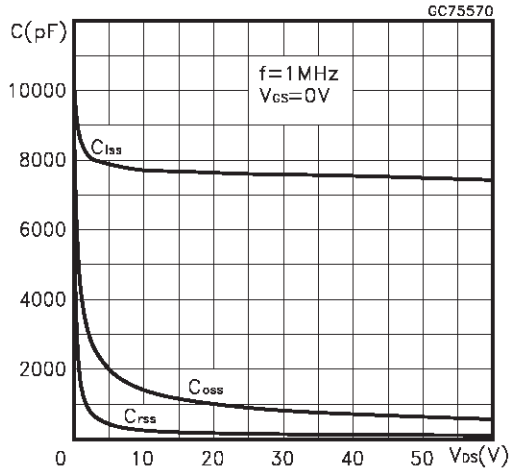
Static Drain-source On Resistance



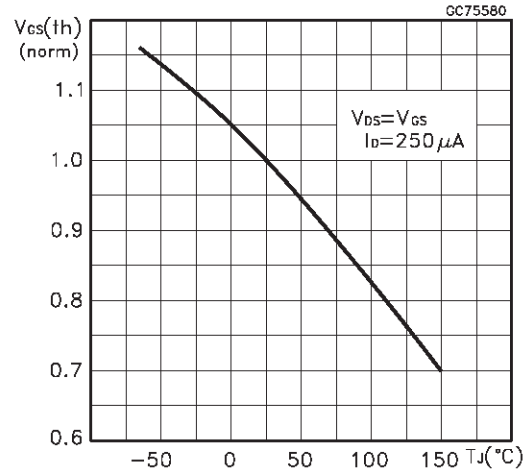
Gate Charge vs Gate-source Voltage



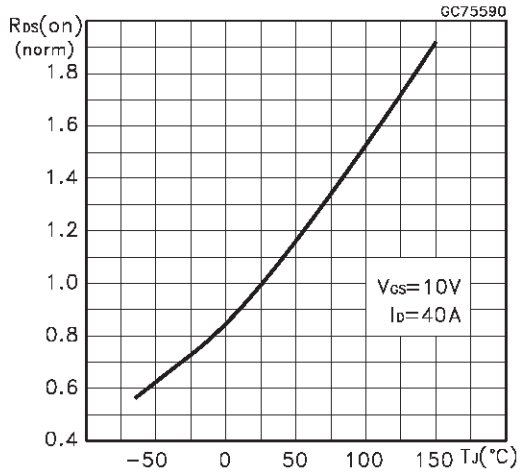
Capacitance Variations



Normalized Gate Threshold Voltage vs Temperature



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

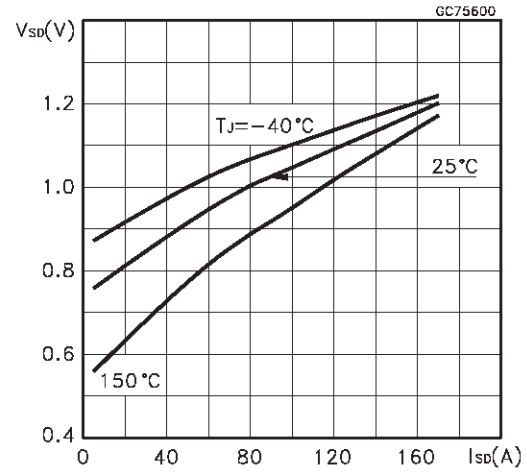


Fig. 1: Unclamped Inductive Load Test Circuit

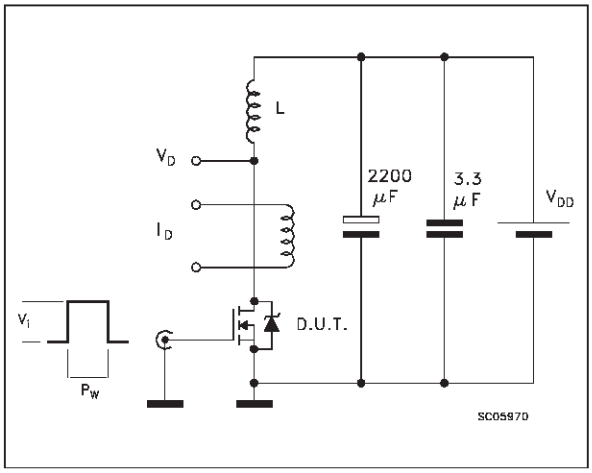


Fig. 2: Unclamped Inductive Waveform

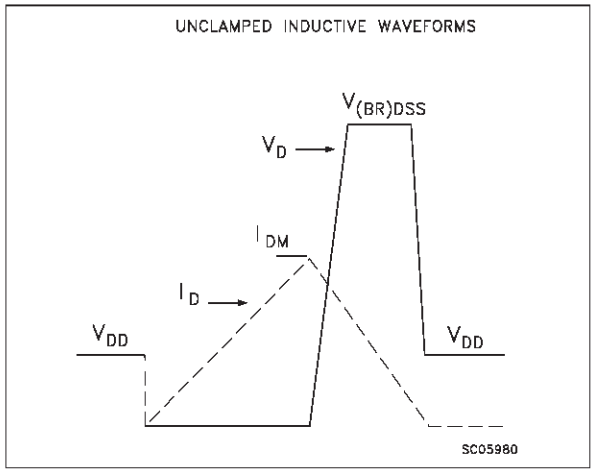


Fig. 3: Switching Times Test Circuits For Resistive Load

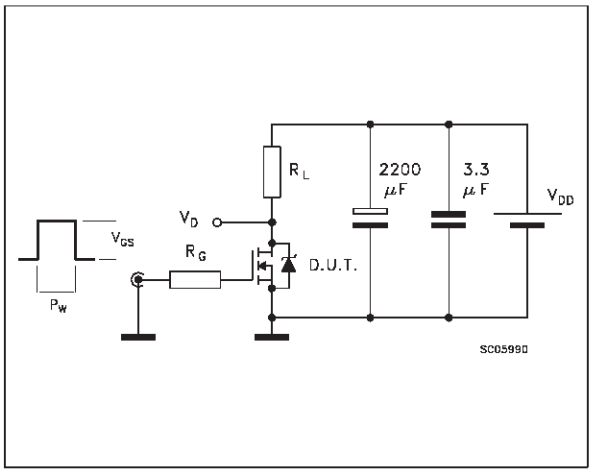


Fig. 4: Gate Charge test Circuit

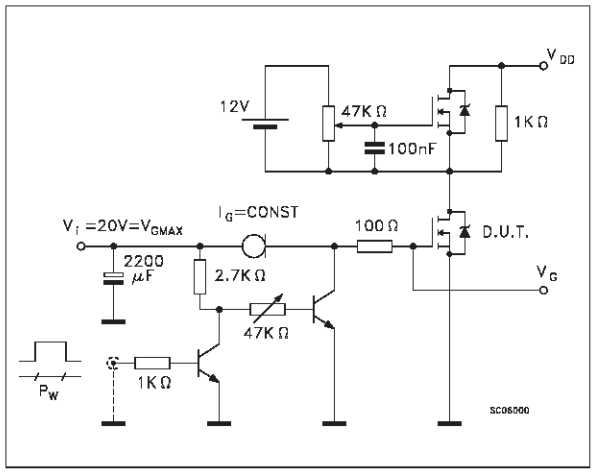
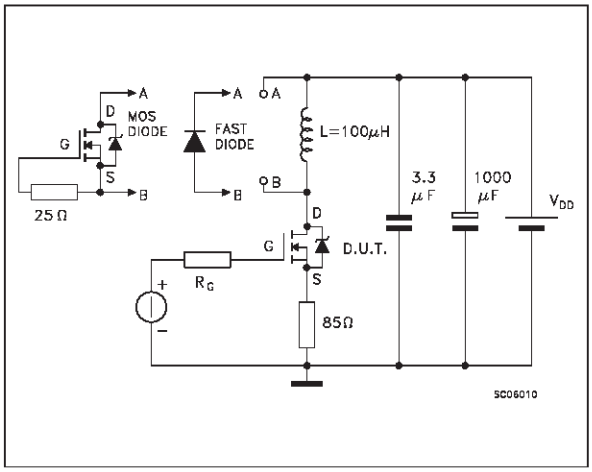
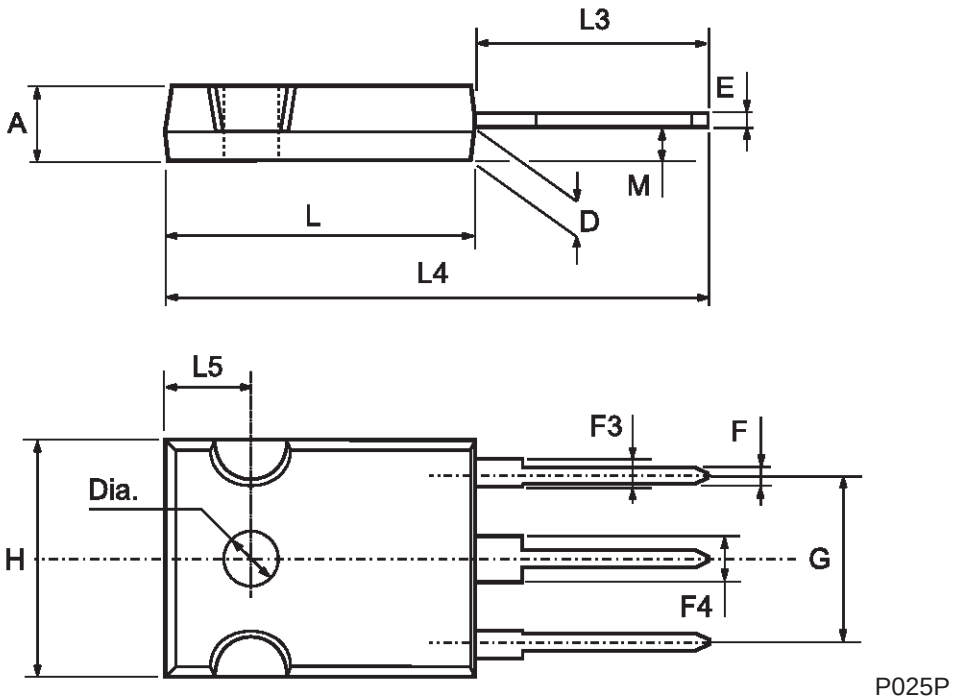


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



TO-247 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.7		5.3	0.185		0.209
D	2.2		2.6	0.087		0.102
E	0.4		0.8	0.016		0.031
F	1		1.4	0.039		0.055
F3	2		2.4	0.079		0.094
F4	3		3.4	0.118		0.134
G		10.9			0.429	
H	15.3		15.9	0.602		0.626
L	19.7		20.3	0.776		0.779
L3	14.2		14.8	0.559	0.413	0.582
L4		34.6			1.362	
L5		5.5			0.217	
M	2		3	0.079		0.118
Dia	3.55		3.65	0.140		0.144



P025P

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specification mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a trademark of STMicroelectronics

© 1998 STMicroelectronics – Printed in Italy – All Rights Reserved

STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - Canada - China - France - Germany - Italy - Japan - Korea - Malaysia - Malta - Mexico - Morocco - The Netherlands - Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A.

.